

Features

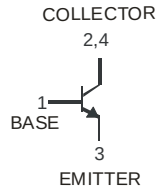
- Ideal for Medium Power Switching or Amplification Applications
- Complementary PNP Type Available (DSS60600MZ4)
- Ultra Low Collector-Emitter Saturation Voltage
- Ideally Suited for Automated Assembly Processes
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**

Mechanical Data

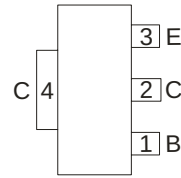
- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.115 grams (approximate)



Top View



Device Schematic



Pin Out Configuration

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	6	V
Peak Pulse Collector Current	I_{CM}	12	A
Continuous Collector Current	I_C	6	A

Thermal Characteristics

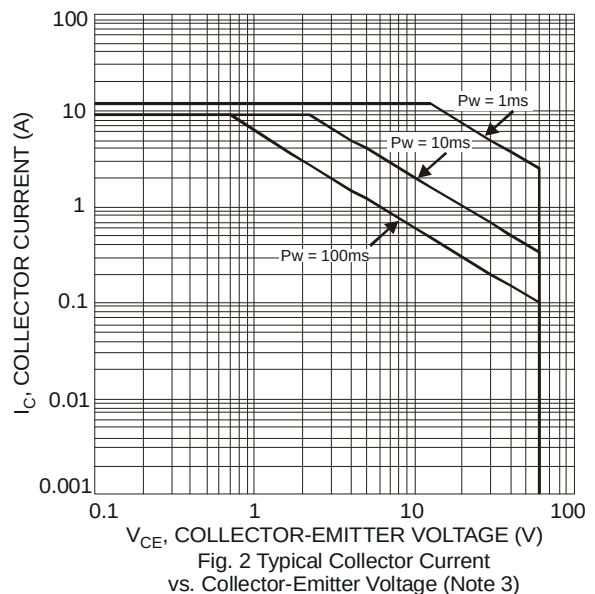
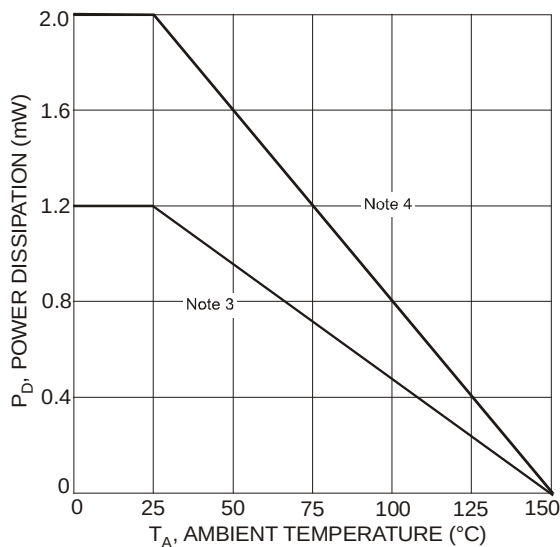
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ $T_A = 25^\circ\text{C}$	P_D	1.2	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	104	$^\circ\text{C/W}$
Power Dissipation (Note 4) @ $T_A = 25^\circ\text{C}$	P_D	2	W
Thermal Resistance, Junction to Ambient Air (Note 4) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB with minimum recommended pad layout.
 4. Device mounted on Polyimide PCB with 330mm² 2 oz. Copper pad layout.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	100	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 5)	V _{(BR)CEO}	60	—	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6	—	—	V	I _E = 100μA
Collector-Base Cutoff Current	I _{CBO}	—	—	100	nA	V _{CB} = 40V, I _E = 0
		—	—	50	μA	V _{CB} = 40V, I _E = 0, T _A = 150°C
Emitter-Base Cutoff Current	I _{EBO}	—	—	100	nA	V _{EB} = 6V, I _C = 0
ON CHARACTERISTICS (Note 5)						
DC Current Gain	h _{FE}	150	—	—	—	V _{CE} = 2V, I _C = 0.5A
		120	—	360	—	V _{CE} = 2V, I _C = 1A
		100	—	—	—	V _{CE} = 2V, I _C = 2A
		50	—	—	—	V _{CE} = 2V, I _C = 6A
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	—	40	mV	I _C = 0.1A, I _B = 2.0mA
		—	—	60	mV	I _C = 1A, I _B = 100mA
		—	80	100	mV	I _C = 2A, I _B = 200mA
		—	—	220	mV	I _C = 3A, I _B = 60mA
		—	—	300	mV	I _C = 6A, I _B = 600mA
Equivalent On-Resistance	R _{CE(SAT)}	—	40	50	mΩ	I _E = 2A, I _B = 200mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	—	0.9	V	I _C = 1A, I _B = 100mA
Base-Emitter Turn-on Voltage	V _{BE(ON)}	—	—	0.9	V	V _{CE} = 2V, I _C = 1A
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	100	—	—	MHz	V _{CE} = 10V, I _C = 100mA, f = 100MHz
Output Capacitance	C _{obo}	—	26	—	pF	V _{CB} = 10V, f = 1MHz
Input Capacitance	C _{ibo}	—	325	—	pF	V _{EB} = 5V, f = 1MHz

Notes: 5. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.



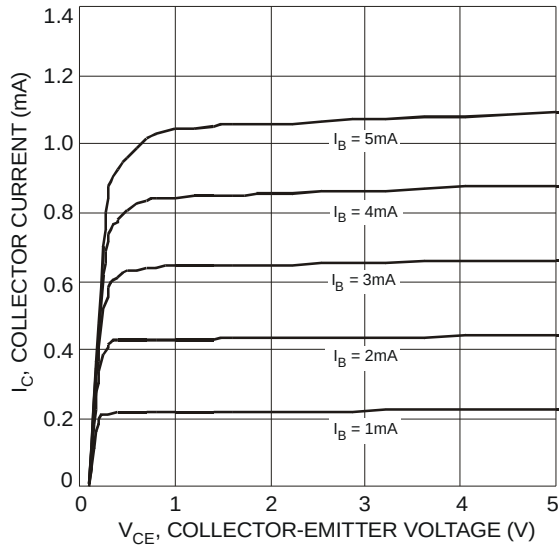


Fig. 3 Typical Collector Current vs. Collector-Emitter Voltage

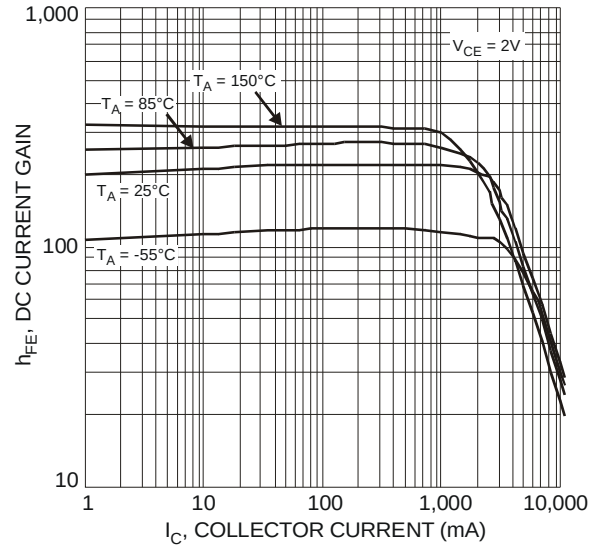


Fig. 4 Typical DC Current Gain vs. Collector Current

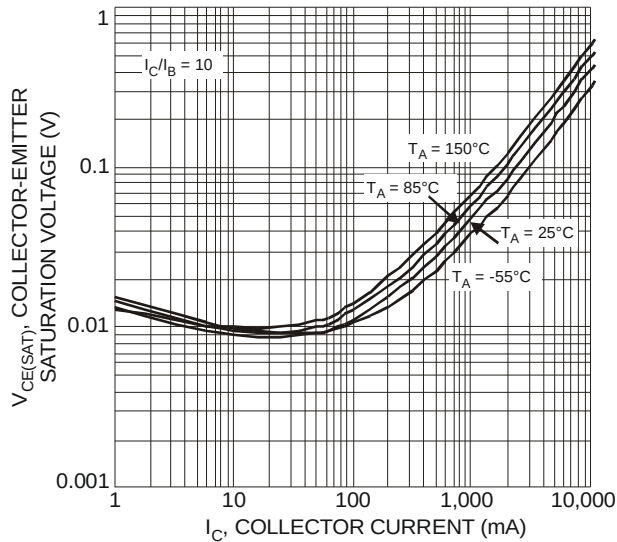


Fig. 5 Typical Collector-Emitter Saturation Voltage vs. Collector Current

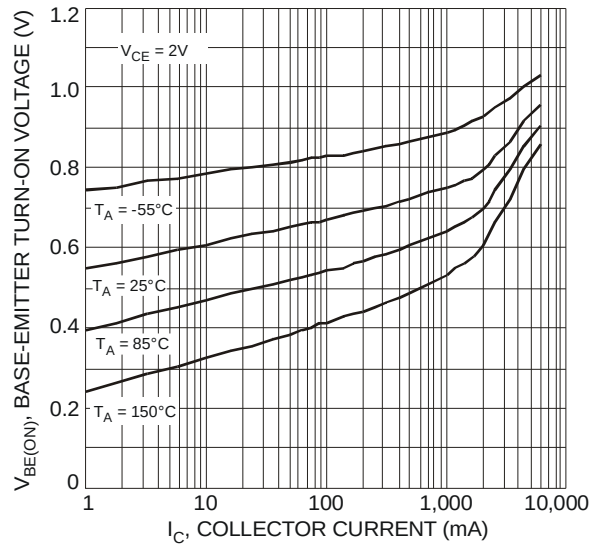


Fig. 6 Typical Base-Emitter Turn-On Voltage vs. Collector Current

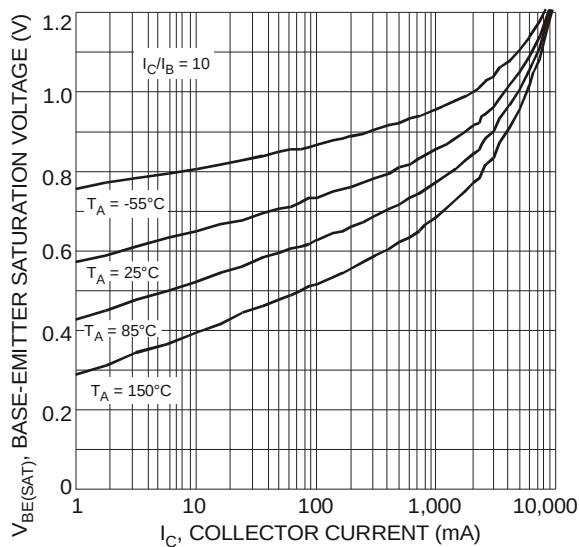


Fig. 7 Typical Base-Emitter Saturation Voltage vs. Collector Current

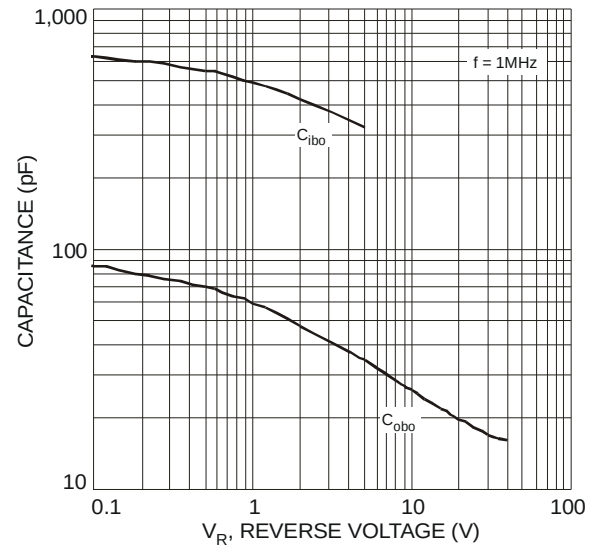


Fig. 8 Typical Capacitance Characteristics

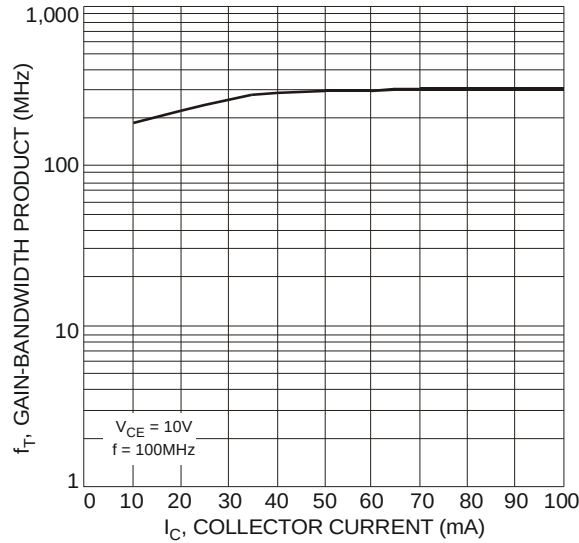


Fig. 9 Typical Gain-Bandwidth Product vs. Collector Current

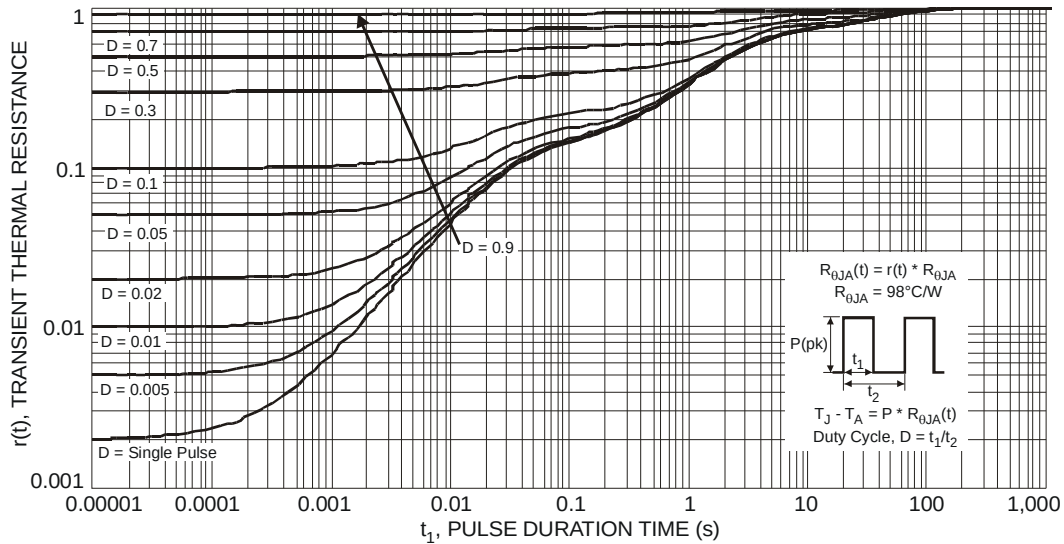


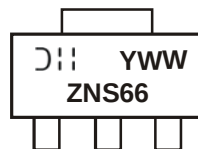
Fig. 10 Transient Thermal Response

Ordering Information (Note 6)

Part Number	Case	Packaging
DSS60601MZ4-13	SOT-223	2500/Tape & Reel

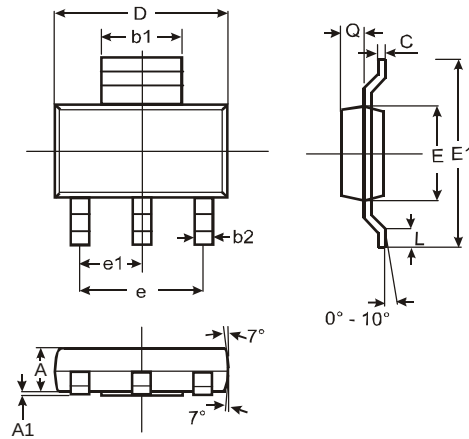
 Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



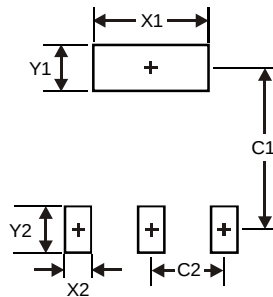
ZNS66 = Product Type Marking Code
 YWW = Date Code Marking
 Y = Last digit of year (ex: 8 = 2008)
 WW = Week code 01 - 52

Package Outline Dimensions



SOT-223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b1	2.90	3.10	3.00
b2	0.60	0.80	0.70
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	—	—	4.60
e1	—	—	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3

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